

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior listing of claims in this application.

Claims 1-25 (canceled).

26. (currently amended) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition comprising:

a flowing plasma etchant mixture consisting essentially of at least one fluorocarbon and ammonia, wherein ~~said ammonia has a flow rate that is from about 2~~
~~seem to about 6 seem~~ the flow rate ratio of each fluorocarbon to ammonia is from about 2:1 to about 40:1.

27. (previously presented) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (original) The composition of claim 27, wherein said fluorocarbon is at least one member selected from the group consisting of C₄F₈, C₄F₆, C₅F₈, CF₄, C₂F₆, C₃F₈, CHF₃, and CH₂F₂.

29. (original) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of CF₄, CHF₃, and CH₂F₂.

30. (original) The composition of claim 29, wherein said fluorocarbon is at least two members selected from the group consisting of CF₄, CHF₃, and CH₂F₂.

31. (original) The composition of claim 30, wherein said fluorocarbon is a combination of CF₄, CHF₃, and CH₂F₂.

32. (previously presented) The composition of claim 26, wherein said composition is ineffective to remove side wall spacers of a gate stack formed over said substrate.

33. (canceled).

34. (currently amended) The composition of claim ~~[[33]]~~ 26, wherein said flow rate ratio is within the range of from about 3:1 to about 20:1.

35. (currently amended) The composition of claim 34, wherein said flow rate ratio is within the range of from about 4:1 to about 10:1.

Claims 36-70 (canceled).

71. (currently amended) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

~~a flowing plasma etchant mixture consisting of at least one fluorocarbon and ammonia under an operating pressure of from about 30 to about 60 milliTorr, comprising at least CF_4 and NH_3 , wherein the flow rate ratio of said at least one fluorocarbon to said ammonia $\text{CF}_4:\text{NH}_3$ is from about 2:1 to about 40:1~~ greater than about 3:1.

72. (currently amended) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

~~a flowing plasma etchant mixture consisting of at least one fluorocarbon and ammonia under an operating temperature of from about -50°C to about 80°C , comprising at least CHF_3 and ammonia, wherein said ammonia has a flow rate that is from about 2 sccm to about 6 sccm~~ the flow rate of said CHF_3 is from about 37 to 42 sccm.

Claims 73-76 (canceled).